

January 20, 2011

Product Specifications of the NE3520S03 FET

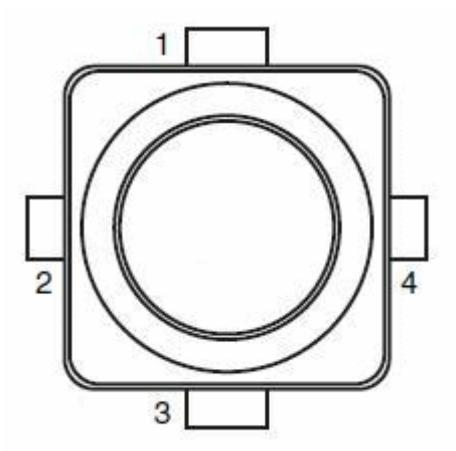
Features

- Recommended bias condition: $V_{DS} = 2\text{ V}$, $I_D = 10\text{ mA}$
- Noise figure (NF): 0.65 dB TYP. (@f = 20 GHz)
- Associated gain (Ga): 13.5 dB TYP. (@f = 20 GHz)
- Package: 4-pin micro-X plastic hollow package (S03)
- Pb (Lead)-free products

Applications

- Ka band (20 GHz band) direct broadcast satellite (DBS) reception system LNB (LNB: Low noise block converter)
- Others, such as K band low noise amplifier for communication system

Pin Connections



1. Source
2. Drain
3. Source
4. Gate